PDFN5×6A MOS

Complementary Enhancement MOSFET in a PDFN5 × 6A Plastic Package.

N-channel	P-channel
V_{DS}(V)=30V	V_{DS}(V)=-30V
I_D=39.5A	I_D=-39A
$R_{DS(ON)}$<10mq(V_{GS}=10V)	$R_{DS(ON)}$<12mq(V_{GS}=-10V)
$R_{DS(ON)}$<15mq(V_{GS}=4.5V)	$R_{DS(ON)}$<20mq(V_{GS}=-4.5V)

HF Product.

DC/DC

These devices are well suited for 1

Parameter

N-

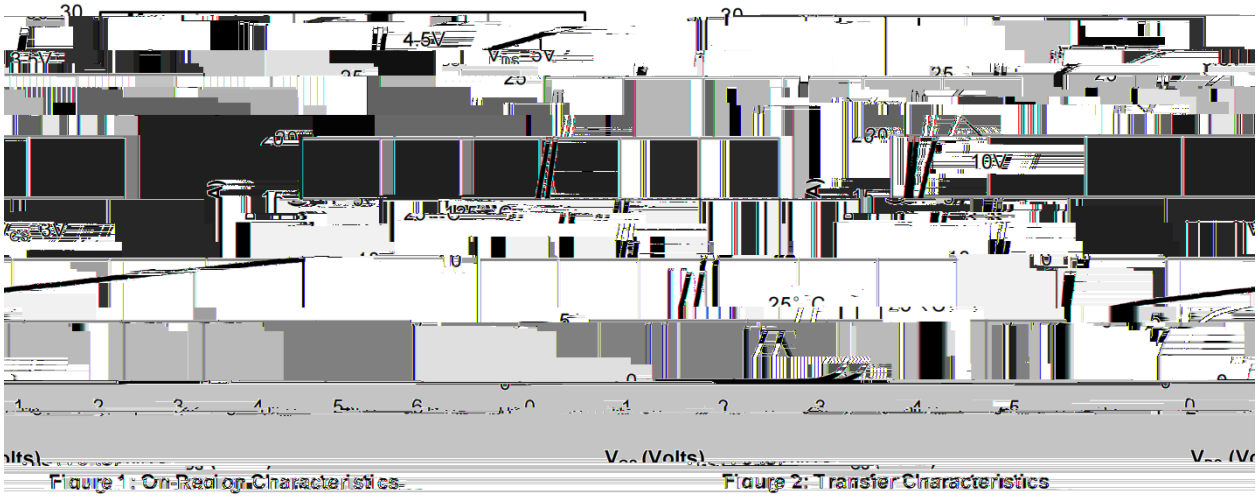


Figure 1: On-Region Characteristics

Figure 2: Transfer Characteristics

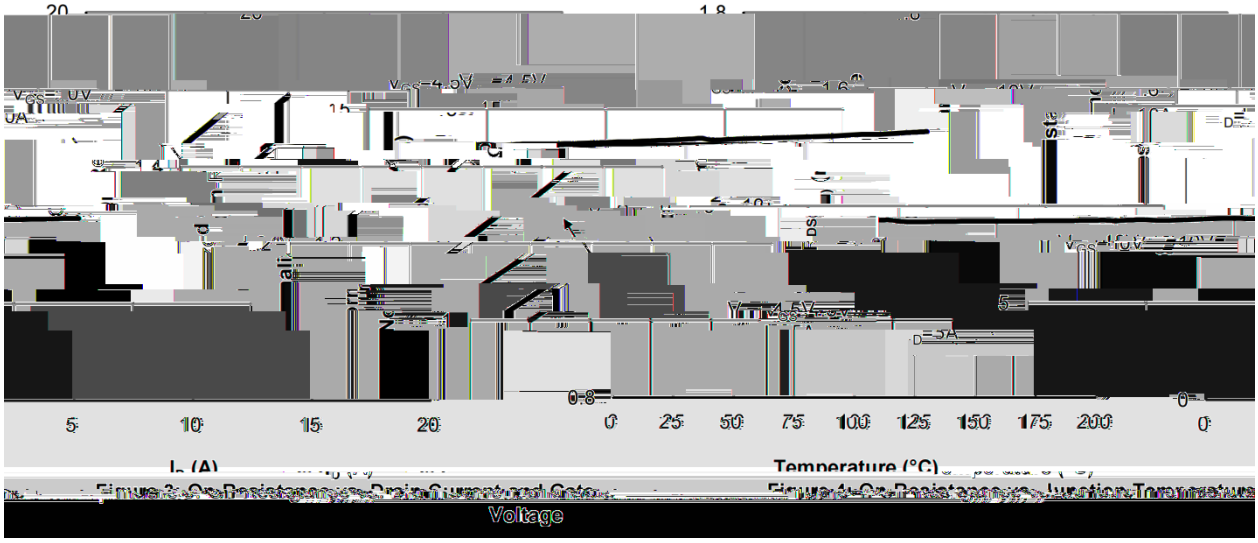
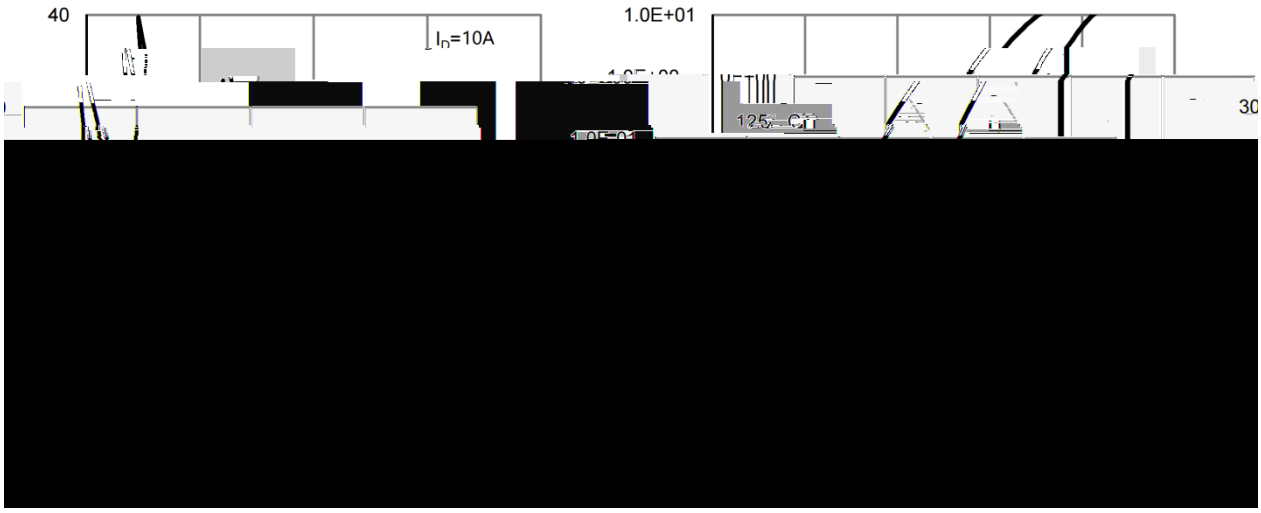


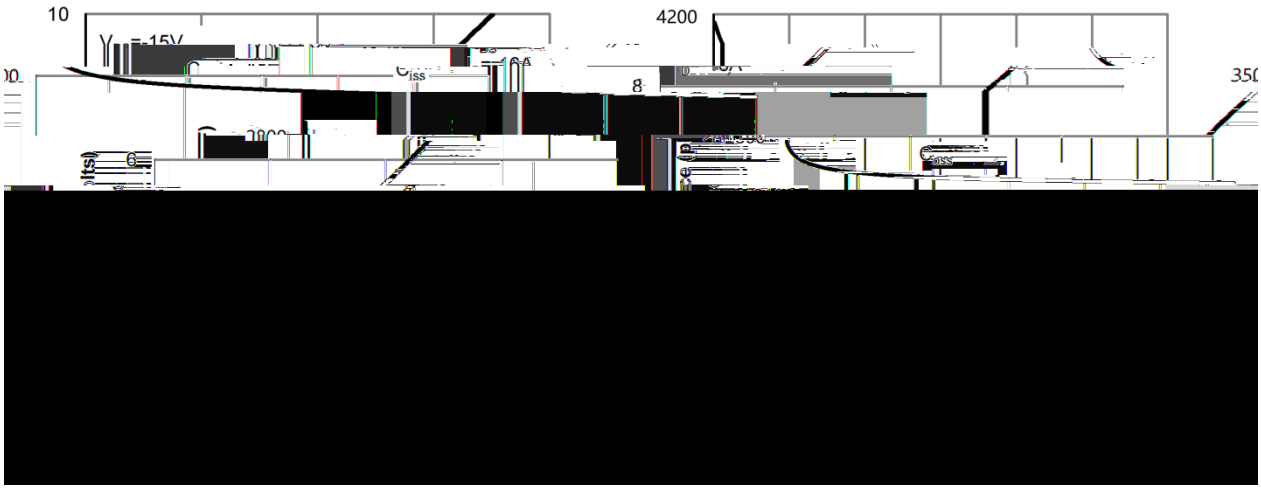
Figure 3: On-Resistance vs. Drain Current and Gate Voltage

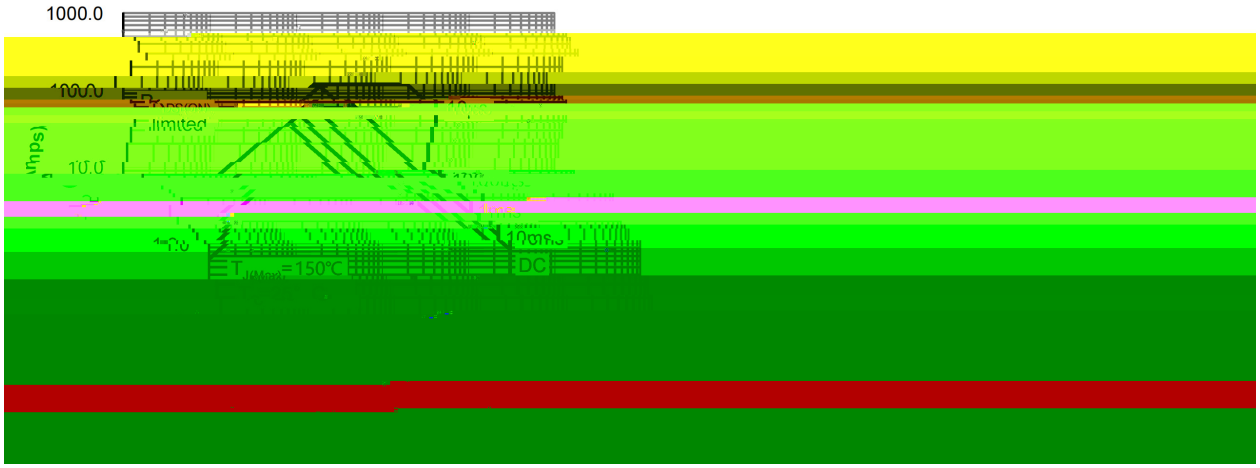
Figure 4: On-Resistance vs. Junction Temperature

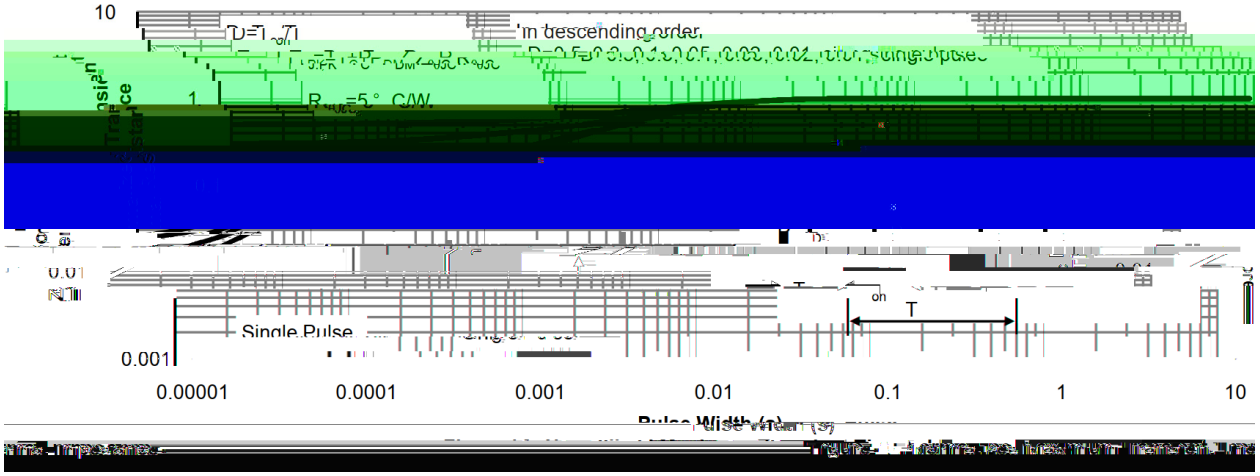


Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown						

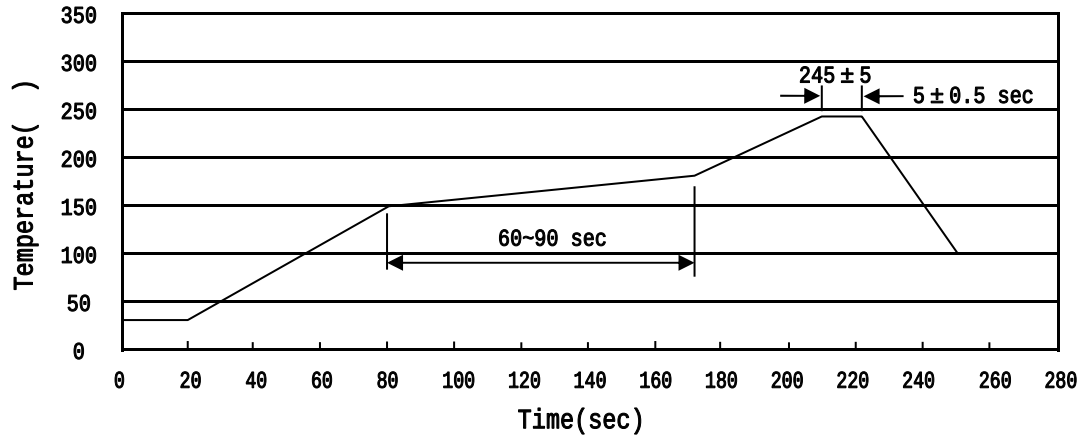
P-


10
4200
350


1000.0
10.0
1.0
Limited
10ms
DC
=150℃


10
1
0.01
0.001
Single Pulse
T
0.00001
0.0001
0.001
0.01
0.1
1
10

Temperature Profile for IR Reflow Soldering(Pb-Free)



		Note:	
1	150 180 60 90sec;	1.Preheating:150~180 , Time:60~90sec.	
2	245±5 5±0.5sec;	2.Peak Temp.:245±5 , Duration:5±0.5sec.	
3	2 10 /sec.	3. Cooling Speed: 2~10 /sec.	

260±5	10±1 sec.	Temp.:260±5	Time:10±1 sec

/ REEL

Package Type	Units					Dimension		(unit mm³)
	Units/Reel /	Reels/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Reel	Inner Box	Outer Box
PDFN5×6A	5,000	2	10,000	6	60,000	13''×12	360×360×50	380×335×366